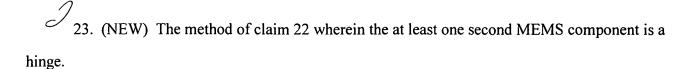
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- 24. (NEW) The method of claim 23 wherein the at least one MEMS component is a mirror retained by the hinge.
- 25. (NEW) The method of claim 21 wherein depositing at least one layer of polysilicon includes chemical vapor deposition.
- 26. (NEW) The method of claim 25 wherein depositing at least one layer of polysilicon includes low pressure chemical vapor deposition.
- 27. (NEW) The method of claim 21 wherein forming at least one first MEMS component includes forming a deflecting mirror.
- 28. (NEW) The method of claim 27 further comprising forming at least one second MEMS component by patterning the polysilicon, the at least one second MEMS component including a hinge retaining the deflecting mirror.
- 29. (NEW) The method of claim 28 wherein forming at least one first MEMS component further includes forming a torsional mirror, and the method further comprises forming a recess in the SOI wafer and mounting a light emitter in the recess so that it will emit light at the deflecting mirror, which deflects light to the torsional mirror.

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- at least one single crystal silicon component bonded to an insulator that rests on a handle wafer; and
- at least one polysilicon component derived from a layer of polysilicon applied over the at least one single crystalline silicon component.
- 31. (NEW) The MEMS device of claim 30 wherein the at least one single crystal silicon component comprises a deflecting mirror.
- 32. (NEW) The MEMS device of claim 31 wherein the at least one polysilicon component comprises a hinge retaining the deflecting mirror.
- 33. (NEW) The MEMS device of claim 30 wherein the at least one single crystal silicon component comprises a torsional mirror.
- 34. (NEW) The MEMS device of claim 30 wherein the at least one polysilicon component comprises a hinge.
 - 35. (NEW) The MEMS device of claim 30 further comprising:
 a recess in the handle wafer aligned with the at least one single crystal silicon component;
 and
 - a semiconductor light emitter mounted in the recess and oriented to emit a light beam at the single crystal silicon component.
- 36. (NEW) The MEMS device of claim 35 wherein the at least one single crystal silicon component comprises a deflecting mirror at which the light beam is directed and a torsional mirror to which the deflecting mirror deflects the light beam, and the at least one polysilicon component comprises a hinge retaining the deflecting mirror.